National Semiconductor

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MM54HC283/MM74HC283
4-Bit Binary Adder with Fast Carry

General Description

This full adder performs the addition of two 4-bit binary numbers utilizing advanced silicon-gate CMOS technology. The sum (Σ) outputs are provided for each bit and the resultant carry (C4) is obtained from the fourth bit. These adders feature full internal look ahead across all four bits. This provides the system designer with partial look-ahead performance at the economy and reduced package count of a ripple-carry implementation.

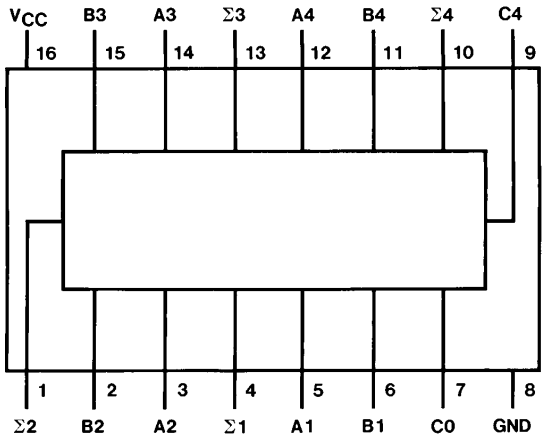
The adder logic, including the carry, is implemented in its true form meaning that the end-around carry can be accomplished without the need for logic or level inversion. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Full-carry look-ahead across the four bits
- Systems achieve partial look-ahead performance with the economy of ripple carry
- Wide supply range: 2V to 6V
- Low quiescent power consumption: 8 μA at 25°C
- Low input current: 1 μA maximum

Connection Diagram

Dual-In-Line Package



TL/F/5332–1

Top View

Order Number MM54HC283 or MM74HC283

RRD-B30M105/Printed in U. S. A.

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	−0.5 to +7.0V
DC Input Voltage (V_{IN})	−1.5 to V_{CC} +1.5V
DC Output Voltage (V_{OUT})	−0.5 to V_{CC} +1.5V
Clamp Diode Current (I_{IK}, I_{OK})	±20 mA
DC Output Current, per pin (I_{OUT})	±25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	±50 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D) (Note 3)	600 mW
S.O. Package only	500 mW
Lead Temperature (T_L) (Soldering 10 seconds)	260°C

Operating Conditions

		Min	Max	Units
Supply Voltage (V_{CC})		2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})		0	V_{CC}	V
Operating Temp. Range (T_A)				
MM74HC		−40	+85	°C
MM54HC		−55	+125	°C
Input Rise or Fall Times (t_r, t_f)	V_{CC} = 2.0V		1000	ns
	V_{CC} = 4.5V		500	ns
	V_{CC} = 6.0V		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V_{CC}	T_A = 25°C	74HC T_A = −40 to 85°C	54HC T_A = −55 to 125°C	Units
				Typ	Guaranteed Limits		
V_{IH}	Minimum High Level Input Voltage		2.0V		1.5	1.5	1.5	V
			4.5V		3.15	3.15	3.15	V
			6.0V		4.2	4.2	4.2	V
V_{IL}	Maximum Low Level Input Voltage**		2.0V		0.5	0.5	0.5	V
			4.5V		1.35	1.35	1.35	V
			6.0V		1.8	1.8	1.8	V
V_{OH}	Minimum High Level Output Voltage	V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 20\ \mu A$	2.0V	2.0	1.9	1.9	1.9	V
			4.5V	4.5	4.4	4.4	4.4	V
			6.0V	6.0	5.9	5.9	5.9	V
		V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 4.0$ mA	4.5V	4.2	3.98	3.84	3.7	V
		$\|I_{OUT}\| \le 5.2$ mA	6.0V	5.7	5.48	5.34	5.2	V
V_{OL}	Maximum Low Level Output Voltage	V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 20\ \mu A$	2.0V	0	0.1	0.1	0.1	V
			4.5V	0	0.1	0.1	0.1	V
			6.0V	0	0.1	0.1	0.1	V
		V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 4.0$ mA	4.5V	0.2	0.26	0.33	0.4	V
		$\|I_{OUT}\| \le 5.2$ mA	6.0V	0.2	0.26	0.33	0.4	V
I_{IN}	Maximum Input Current	V_{IN} = V_{CC} or GND	6.0V		±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	V_{IN} = V_{CC} or GND I_{OUT} = 0 μA	6.0V		8.0	80	160	μA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: −12 mW/°C from 65°C to 85°C; ceramic "J" package: −12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} = 5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

**V_{IL} limits are currently tested at 20% of V_{CC}. The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics $V_{CC} = 5V$, $T_A = 25°C$, $C_L = 15$ pF, $t_r = t_f = 6$ ns

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL}, t_{PLH}	Maximum Propagation Delay From C0 to Σ1 or Σ2		18	27	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay From C0 to Σ3		18	27	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay From C0 to Σ4		20	30	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay From A1 or B1 to Σ1		17	26	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay From C0 to C4		22	32	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay From A1 or B1 to C4		22	32	ns

AC Electrical Characteristics $C_L = 50$ pF, $t_r = t_f = 6$ ns (unless otherwise specified)

Symbol	Parameter	Conditions	V_{CC}	$T_A = 25°C$		74HC $T_A = -40$ to $85°C$	54HC $T_A = -55$ to $125°C$	Units
				Typ	Guaranteed Limits			
t_{PHL}, t_{PLH}	Maximum Propagation Delay From C0 to Σ1 or Σ2		2.0V	60	150	188	225	ns
			4.5V	21	30	37	45	ns
			6.0V	18	26	32	39	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay From C0 to Σ3		2.0V	60	150	188	225	ns
			4.5V	21	30	37	45	ns
			6.0V	18	26	32	39	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay From C0 to Σ4		2.0V	65	162	202	243	ns
			4.5V	24	34	43	51	ns
			6.0V	19	28	35	42	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay From A1 or B1 to Σ1		2.0V	60	150	188	225	ns
			4.5V	22	33	41	50	ns
			6.0V	18	27	34	41	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay From C0 to C4		2.0V	70	175	219	263	ns
			4.5V	26	39	49	59	ns
			6.0V	21	32	40	46	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay From A1 or B1 to C4		2.0V	70	175	219	263	ns
			4.5V	26	39	49	59	ns
			6.0V	21	32	40	46	ns
t_{THL}, t_{TLH}	Maximum Output Rise and Fall Time		2.0V	28	75	95	110	ns
			4.5V	8	15	19	22	ns
			6.0V	7	13	16	19	ns
C_{IN}	Maximum Input Capacitance			6	10	10	10	pF
C_{PD}	Power Dissipation Capacitance (Note 5)			150				pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

Truth Table

Input								Output									
								When C0 = L						When C0 = H			
												When C2 = L					When C2 = H
A1	A3	B1	B3	A2	A4	B2	B4	Σ1	Σ3	Σ2	Σ4	C2	C4	Σ1	Σ3	Σ2	Σ4	C2	C4
L		L		L		L		L		L		L		H		L		L	
H		L		L		L		H		L		L		L		H		L	
L		H		L		L		H		L		L		L		H		L	
H		H		L		L		L		H		L		H		H		L	
L		L		H		L		L		H		L		H		H		L	
H		L		H		L		H		H		L		L		L		H	
L		H		H		L		H		H		L		L		L		H	
H		H		H		L		L		L		H		H		L		H	
L		L		L		H		L		H		L		H		H		L	
H		L		L		H		H		H		L		L		L		H	
L		H		L		H		H		H		L		L		L		H	
H		H		L		H		L		L		H		H		L		H	
L		L		H		H		L		L		H		H		L		H	
H		L		H		H		H		L		H		L		H		H	
L		H		H		H		H		L		H		L		H		H	
H		H		H		H		L		H		H		H		H		H	

H = high level, L = low level

Note: Input conditions at A1, B1, A2, B2, and C0 are used to determine outputs Σ1 and Σ2 and the value of the internal carry C2. The values at C2, A3, B3, A4, and B4 are then used to determine outputs Σ3, Σ4, and C4

Logic Diagram

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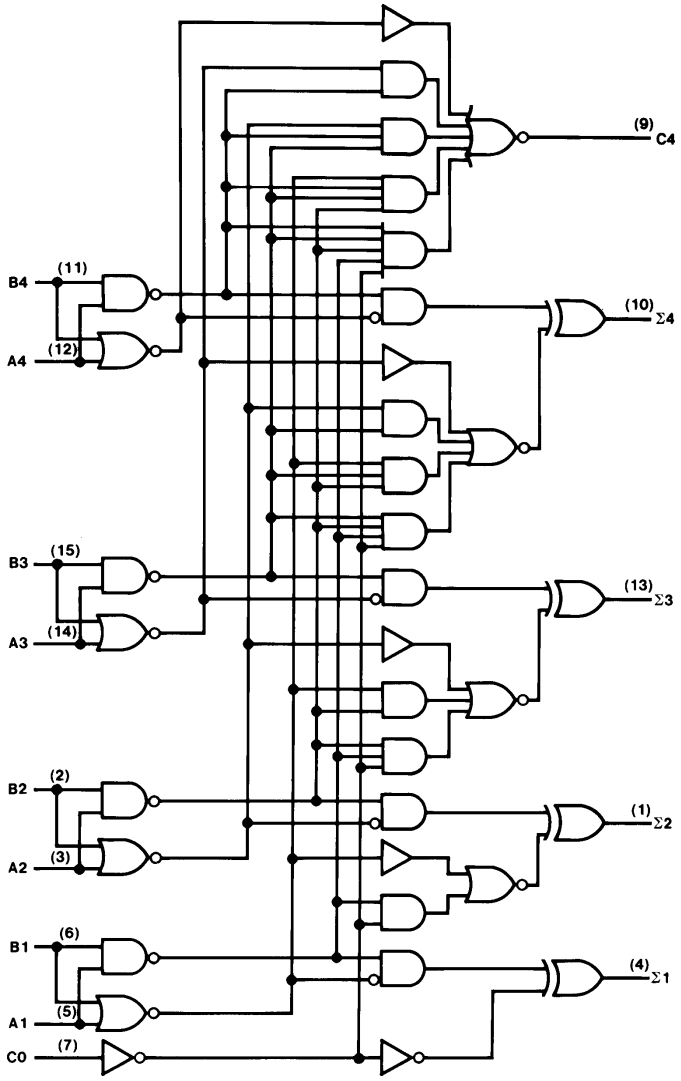

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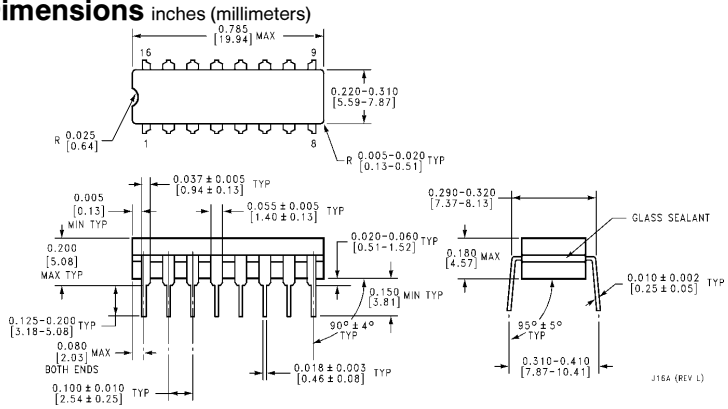
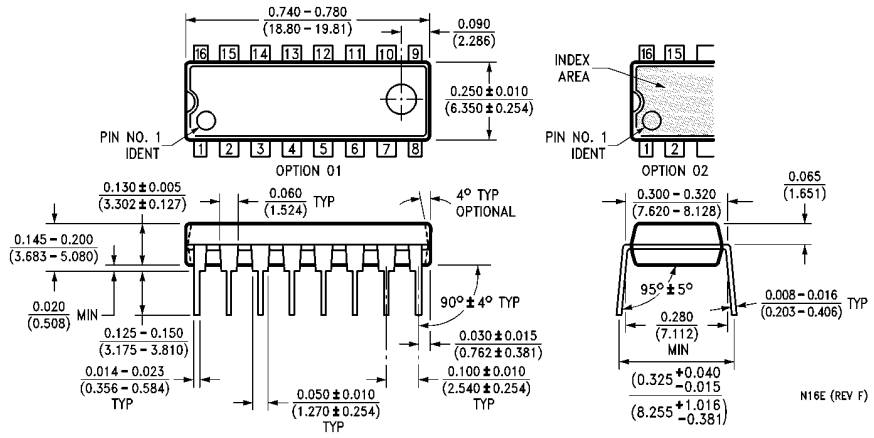
Physical Dimensions inches (millimeters)



Order Number MM54HC283J or MM74HC283J
NS Package J16A



Order Number MM74HC283N
NS Package N16E

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